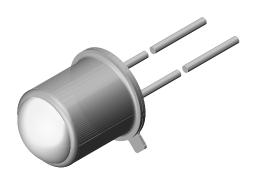


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### **TSTS7300**

## Vishay Semiconductors

# Infrared Emitting Diode, 950 nm, GaAlAs, MQW



#### **DESCRIPTION**

TSTS7300 is an infrared, 950 nm emitting diode in GaAlAs multi quantum well (MQW) technology in a hermetically sealed TO-18 package with lens.

#### **FEATURES**

Package type: leadedPackage form: TO-18

Dimensions (in mm): Ø 4.7
Peak wavelength: λ<sub>p</sub> = 950 nm

High reliability

High radiant power

· High radiant intensity

• Angle of half intensity:  $\phi = \pm 8^{\circ}$ 

· Low forward voltage

· Good spectral matching with Si photodetectors

 Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>



· Radiation source in near infrared range

| PRODUCT SUMMARY |                        |       |                             |                     |  |
|-----------------|------------------------|-------|-----------------------------|---------------------|--|
| COMPONENT       | I <sub>e</sub> (mW/sr) | φ (°) | $\lambda_{\mathbf{p}}$ (nm) | t <sub>r</sub> (ns) |  |
| TSTS7300        | 95                     | ± 8   | 950                         | 15                  |  |

#### Note

· Test conditions see table "Basic Characteristics"

| ORDERING INFORMATION |           |                              |              |  |  |  |
|----------------------|-----------|------------------------------|--------------|--|--|--|
| ORDERING CODE        | PACKAGING | REMARKS                      | PACKAGE FORM |  |  |  |
| TSTS7300             | Bulk      | MOQ: 1000 pcs, 1000 pcs/bulk | TO-18        |  |  |  |

### Note

· MOQ: minimum order quantity

| ABSOLUTE MAXIMUM RATINGS (T <sub>amb</sub> = 25 °C, unless otherwise specified) |                             |                   |             |      |  |
|---|-----------------------------|-------------------|-------------|------|--|
| PARAMETER   | TEST CONDITION              | SYMBOL            | VALUE       | UNIT |  |
| Reverse voltage   |                             | V <sub>R</sub>    | 5           | V    |  |
| Forward current   |                             | I <sub>F</sub>    | 100         | mA   |  |
| Power dissipation   |                             | P <sub>V</sub>    | 170         | mW   |  |
| Junction temperature  |                             | Tj                | 125         | °C   |  |
| Ambient temperature range   |                             | T <sub>amb</sub>  | -40 to +85  | °C   |  |
| Storage temperature range   |                             | T <sub>stg</sub>  | -40 to +110 | °C   |  |
| Soldering temperature   | $t \le 5$ s, 2 mm from case | T <sub>sd</sub>   | 260         | °C   |  |
| Thermal resistance junction to ambient  | J-STD-051                   | R <sub>thJA</sub> | 500         | K/W  |  |





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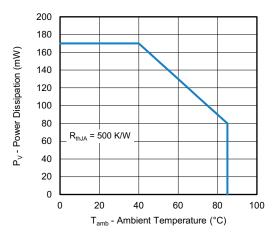


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

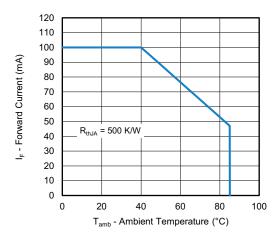


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS (T <sub>amb</sub> = 25 °C, unless otherwise specified) |   |                  |                                    |      |      |       |
|--|---|------------------|------------------------------------|------|------|-------|
| PARAMETER  | TEST CONDITION  | SYMBOL           | MIN.                               | TYP. | MAX. | UNIT  |
| Forward voltage  | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$                     | V <sub>F</sub>   | -                                  | 1.4  | 1.7  | V     |
|  | $I_F = 1 \text{ A}, t_p = 100 \mu \text{s}$                     | V <sub>F</sub>   | -                                  | 2.2  | -    | V     |
| Temperature coefficient of V <sub>F</sub>                                    | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$                     | TK <sub>VF</sub> | -                                  | -1.1 | -    | mV/K  |
| Reverse current  |   | I <sub>R</sub>   | Not designed for reverse operation |      |      | μΑ    |
| Junction capacitance   | $V_R = 0 \text{ V, } f = 1 \text{ MHz, } E = 0 \text{ mW/cm}^2$ | C <sub>j</sub>   | -                                  | 56   | -    | pF    |
| Radiant intensity  | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$                     | l <sub>e</sub>   | 55                                 | 95   | 230  | mW/sr |
| Radiant power  | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$                     | фe               | -                                  | 17   | -    | mW    |
| Temperature coefficient of $\phi_e$  | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$                     | TKφe             | -                                  | -0.5 | -    | %/K   |
| Angle of half intensity  |   | φ                | -                                  | ± 8  | -    | 0     |
| Peak wavelength  | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$                     | $\lambda_{p}$    | -                                  | 950  | -    | nm    |
| Spectral bandwidth   |   | Δλ               | -                                  | 30   | -    | nm    |
| Temperature coefficient of λ <sub>p</sub>                                    | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$                     | TKλ <sub>p</sub> | -                                  | 0.2  | -    | %/K   |
| Rise time  | I <sub>F</sub> = 100 mA   | t <sub>r</sub>   | -                                  | 15   | -    | ns    |
| Fall time  | I <sub>F</sub> = 100 mA   | t <sub>f</sub>   | -                                  | 15   | -    | ns    |

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### **BASIC CHARACTERISTICS** (T<sub>amb</sub> = 25 °C, unless otherwise specified)

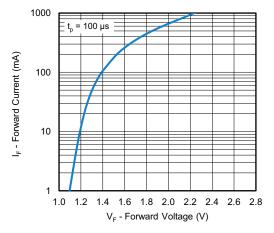


Fig. 3 - Forward Current vs. Forward Voltage

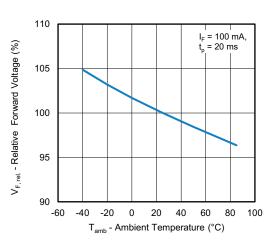


Fig. 4 - Forward Voltage vs. Ambient Temperature

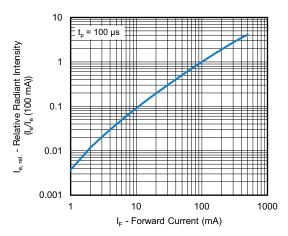


Fig. 5 - Relative Radiant Intensity vs. Forward Current

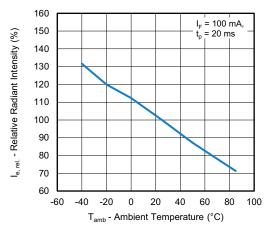


Fig. 6 - Relative Radiant Intensity vs. Ambient Temperature

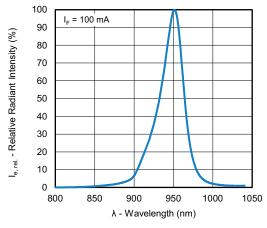


Fig. 7 - Relative Radiant Intensity vs. Wavelength

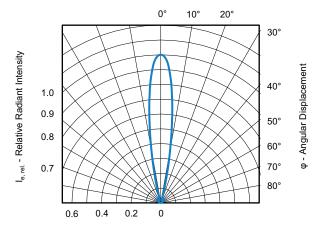


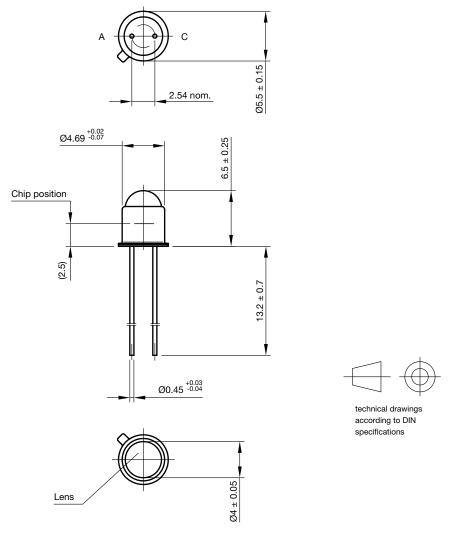
Fig. 8 - Relative Radiant Intensity vs. Angular Displacement



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### **PACKAGE DIMENSIONS** in millimeters



Drawing-No.: 6.503-5022.02-4 Issue: 2VK; 25.03.2024



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